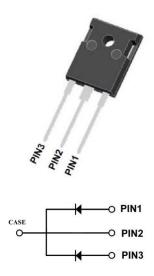


YJD117020NCTG1



Silicon Carbide Schottky Diode

V_{RRM}	1700V
I _{F (135°C)}	36A ⁽²⁾
Qc	170nC ⁽²⁾



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AB
 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D117020NCTG1
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	V	1700
Reverse voltage (Surge Peak) @ Tj=25°C	V_{RSM}	V	1700
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1700
Continuous forward current @ T _c =25°C			38/76
Continuous forward current @ T _c =135°C	I _F	А	18/36
Continuous forward current @ T _c =160°C			10/20
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	64 ⁽¹⁾
Power Dissipation@ T₀=25°C	В	W	234/468
Power Dissipation@ T₀=110°C	Ртот		101/202
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	20 ⁽¹⁾
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

⁽¹⁾ Per Leg, (2) Per Device





■Electrical Characteristics (Per Leg)

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.			
Forward voltage drop	V _F	V	I _F =10A, T _j =25°C	1.4	2.0			
			I _F =10A, T _j =175°C	2.1	-			
Poverse leakage gurrent		l _R μΑ	V _R =1700V, T _j =25°C	1.8	16			
Reverse leakage current	IR		V _R =1700V, T _j =175°C	10	-			
Total capacitive charge	Q _C	nC	V_R =800V, T_j =25°C, $QC = \int_0^{VR} C(V) dV$	85	-			
						V _R =0V, f=1MHZ	1201	-
Total capacitance C	С	pF	V _R =400V, f=1MHZ	78	-			
			V _R =800V, f=1MHZ	64	-			
Capacitance Stored Energy	Ec	μJ	V _R =800V	22	-			

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance R		°C W	0.64 ⁽¹⁾ 0.32 ⁽²⁾

⁽¹⁾ Per Leg, ⁽²⁾ Per Device

■Typical Characteristics (Per Leg)

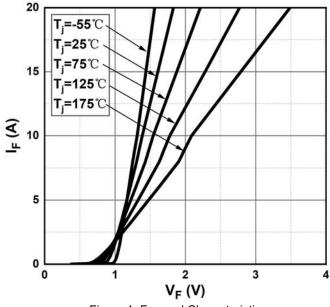


Figure 1. Forward Characteristics

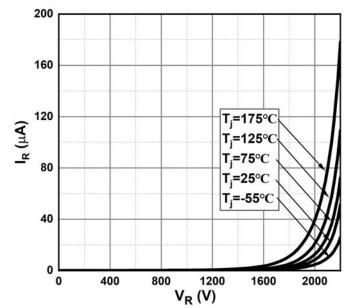
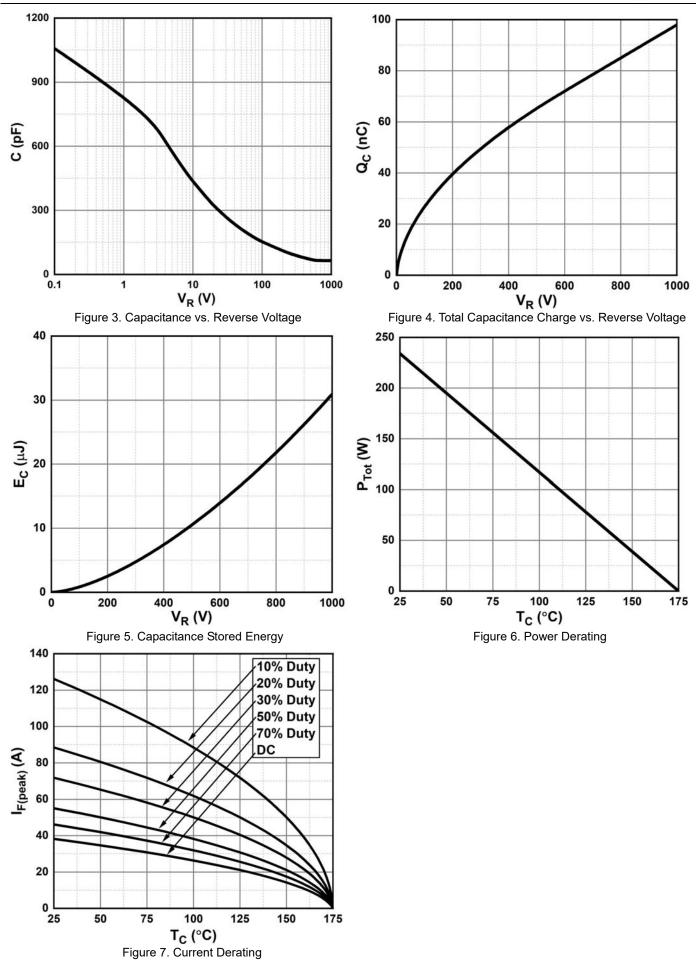


Figure 2. Reverse Characteristics









■Typical Characteristics (Device)

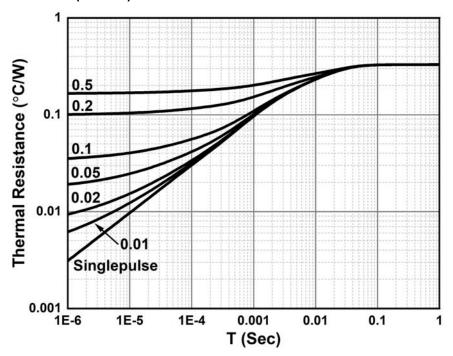


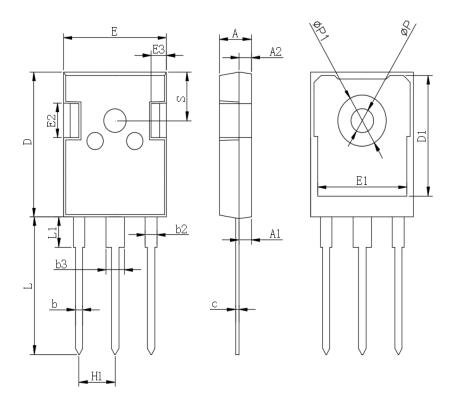
Figure 8. Transient Thermal Impedance





■Outline Dimensions

TO-247AB



TO-247AB				
Dim	Min	Max		
Α	4.80	5.20		
A 1	2.21	2.61		
A2	1.85	2.15		
b	1.0	1.4		
b2	1.91	2.21		
С	0.5	0.7		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.0	13.6		
E2	4.80	5.20		
E3	2.30	2.70		
L	19.62	20.22		
L1	-	4.30		
ΦР	3.40	3.80		
ФР1	-	7.30		
S	6.15TYP			
H1	5.44TYP			
b3	2.80	3.20		



YJD117020NCTG1



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